

## Sputtering TiW on Si using Sputter#4

**Recipe#1: Sputtering Condition:** 4.5mT, 300W, Ar=45sccm, z=1, tilting=10, and time=300 s

Result: the sputtering rate≈4.7nm/min, roughness Ra=0.559 nm.

Figure 1 Film Thickness=23.6nm.

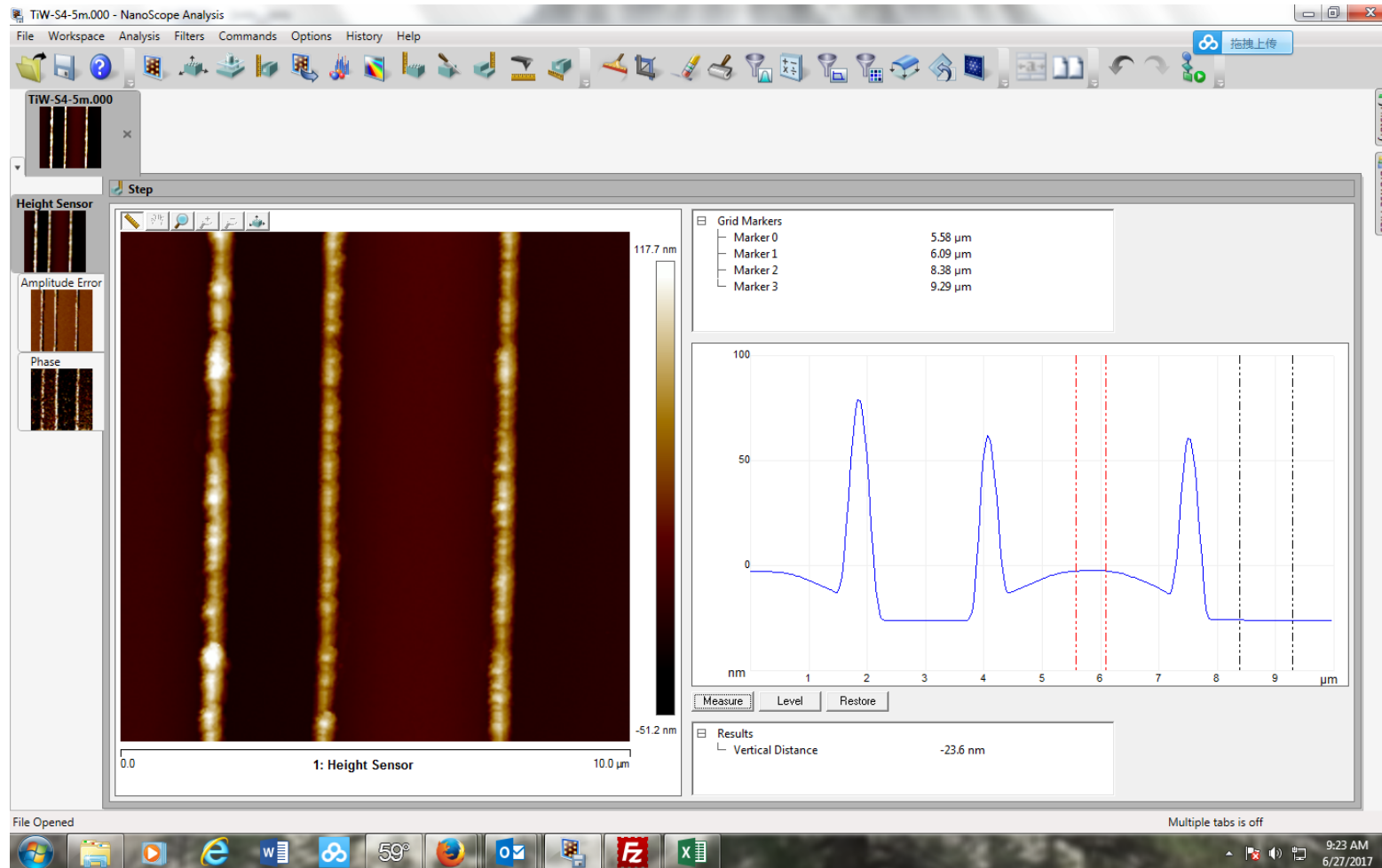


Figure 2 Surface scan by AFM (Ra=0.559 nm)

